

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

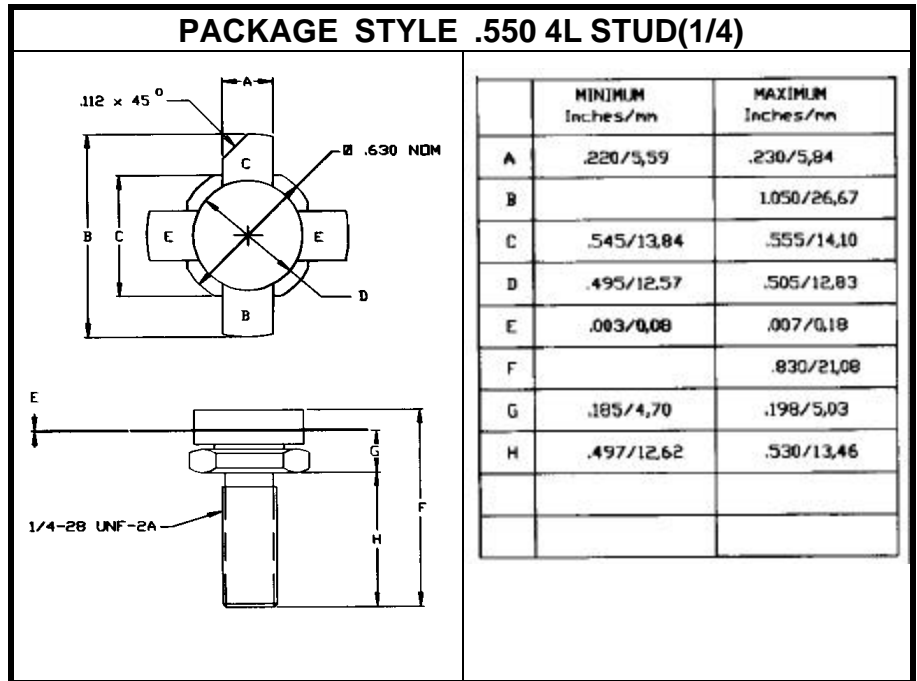
The **ASI TPV376** is a Common Emitter Device Designed for High Linearity Class A Television Band III (170-230 MHz) Applications.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	16 A
<b>V<sub>CB</sub></b>	60 V
<b>P<sub>DISS</sub></b>	150 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>q<sub>JC</sub></b>	1.2 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 100 mA			30			V
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 100 mA	R <sub>BE</sub> = 10 Ω		60			V
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 mA			60			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 20 mA			4.0			V
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V	I <sub>C</sub> = 1.0 A		10		120	---
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 30 V	f = 1.0 MHz				150	pF
<b>P<sub>out</sub></b>	V <sub>CE</sub> = 28 V	I <sub>C</sub> = 3.5 A	f = 225 MHz	20			W
<b>y</b>	V <sub>CE</sub> = 28 V LOAD VSWR = ∞:1	I <sub>E</sub> = 3.5 A	P <sub>REF</sub> = 20 W f = 225 MHz	NO DEGRADATION IN OUTPUT POWER			
<b>IMD<sub>1</sub></b>	P <sub>ref</sub> = 30 W SOUND CARRIER = -7.0 dB V <sub>CE</sub> = 28 V	VISION CARRIER = -8.0 dB SIDE BAND SIG. = -16 dB I <sub>E</sub> = 3.5 A f = 225 MHz				-53	dB



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